SiCウェーハ用高性能研磨スラリー

NANOBIX™

用　途

・SiCウェーハ用、2液混合型研磨スラリー
Polishing slurry mixed of two-component for SiC wafers.

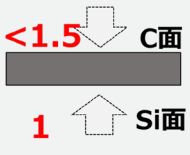
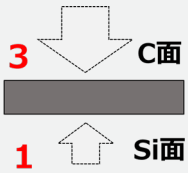
概要・特徴

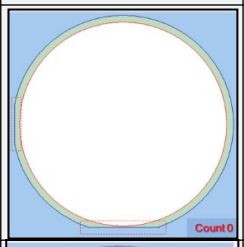
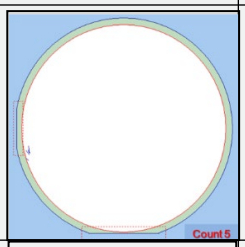
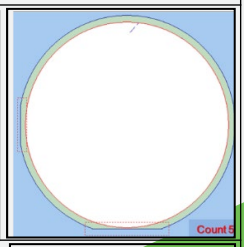
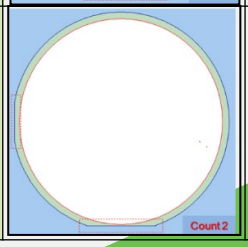
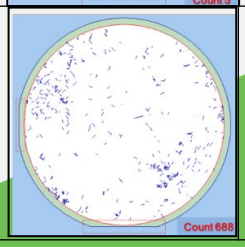
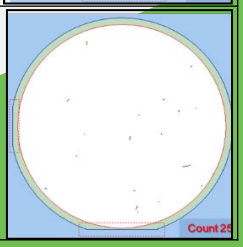
・MnO_2砥粒により1工程でダメージフリーな加工が可能
MnO_2 abrasive enables your polishing w/o damage by one process.

・C面とSi面を同レートで加工可能
C and Si surfaces can be polished at the same rate.

・装置洗浄/ウェハ洗浄が容易
Easy handling for equipment and wafer cleaning

A液　　B液

	NANOBIX™	一般品
砥粒	MnO_2	Al2O3, SiO2
酸化剤	$KMnO_4$	KMnO4
pH	8～9	2～4
研磨レート比		

	NANOBIX™	一般品	
砥粒	MnO_2	Al_2O_3	SiO_2
酸化剤	$KMnO_4$	$KMnO_4$	$KMnO_4$
取り代	3μm	3μm	3μm
CMP後 Ra	0.14nm	0.13nm	0.13nm
CMP後			
H_2エッチング後			

三井金属

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